

Synthesis of Sulfide Perovskites by Sulfurization with Boron Sulfides

Roman Bystrický,^{1,2} Sameer K. Tiwari,¹ Peter Hutár,^{1,3} Ľubomír Vančo,⁴ and Milan Sýkora^{1*}

¹Laboratory for Advanced Materials, Faculty of Natural Sciences, Comenius University, Ilkovičova 6, 842 15 Bratislava, Slovakia, ²Institute of Inorganic Chemistry, Slovak Academy of Sciences, Dúbravská cesta 9, 845 36 Bratislava, Slovakia, ³Institute of Electrical Engineering, Slovak Academy of Sciences, Dúbravská cesta 9, 841 04 Bratislava, Slovakia, ⁴Centre for Nanodiagnostics of Materials, Faculty of Materials Science and Technology, Slovak University of Technology, Vazovova 5, 812 43 Bratislava, Slovakia

Supporting Information Placeholder

ABSTRACT: Chalcogenide perovskites (CPs), with general composition ABX_3 , where A and B are metals and $X = S, Se$, have recently emerged as promising materials for application in photovoltaics. However, the development of the CPs and their applications has been hindered by limitations of the available preparation methods. Here we present a new approach for synthesis of CPs, based on sulfurization of ternary and binary oxides or carbonates with in-situ formed boron sulfides. In contrast to the previously described approaches, the method presented here uses chemically stable starting materials and yields pure phase crystalline CPs within several hours, under low hazard conditions. CP yields over 95% are obtained at temperatures as low as 600 °C. The generality of the approach is demonstrated by preparation of CPs with compositions Ba-ZrS₃, β-SrZrS₃, BaHfS₃, SrHfS₃ and EuHfS₃. Mechanistic insights about the formation of CPs are discussed.

A great level of interest in solid materials with perovskite crystalline structure in recent years has been stimulated primarily by a discovery that a subset of these materials, halide-perovskites (HPs), possess combination of properties excellent for exploitation in photovoltaics and more broadly optoelectronics.¹⁻² Integration of HPs into thin-film solar cells led to unprecedented performance enhancements.³ HPs were also shown to be very promising materials for development of efficient light emitting diodes, lasers, detectors and other technologies.⁴⁻⁷ Despite the promise of HPs, their limited thermal and chemical stability and inclusion of toxic ions, such as lead, pose challenge for their commercial exploitation.

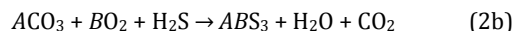
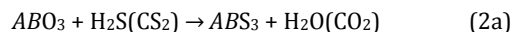
Chalcogenide perovskites (CPs), crystalline solids with the composition ABX_3 , where A, B , are metal cations and $X = S, Se$, have been recently suggested as a possible alternative to the structurally related HPs.⁸⁻¹¹ Although more research is needed to fully assess their potential, theoretical¹²⁻¹³ and early experimental¹³⁻¹⁵ studies indicate that CPs have electronic properties similar to the HPs, are comparable or better light absorbers,^{13, 16} have better chemical and thermal stability¹⁷⁻¹⁸ and can be prepared without the use of toxic elements. Experimental studies of the CPs have so far been limited, however, mainly due to the challenges with their preparation.

To date, all known CPs (all sulfides)¹¹ were prepared by one of two solid-state, high-temperature (>600 °C) syntheses methods, first described more than sixty years ago.¹⁹⁻²⁰ In one method, the elements and/or binary sulfides are reacted in sealed, evacuated reaction tubes, according to Eq. (1):



The second method is based on sulfurization of oxide or

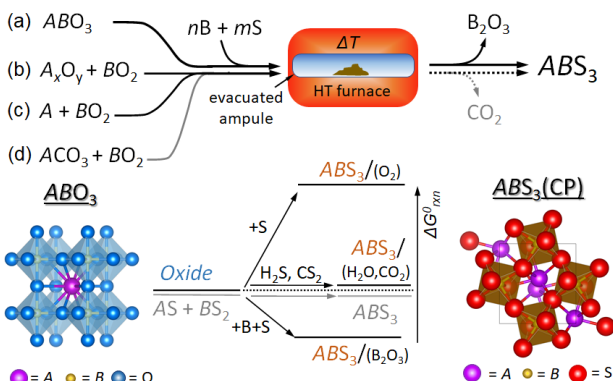
carbonate precursors with H₂S or CS₂ gas at temperatures >1000 °C, according to Eq. (2):



In equations (1) and (2), the typical examples of ion A are Ca²⁺, Sr²⁺, Ba²⁺, Ln^{2+/3+}, and B are Zr⁴⁺, Hf⁴⁺, Sc³⁺, Ln^{3+/4+} (Ln = Lanthanide). One drawback of both methods is long reaction time, with days-to-weeks often required for complete conversion. Another drawback of approach (1) is a high propensity of the starting materials A, B, AS, BS_2 to oxidation even at ambient conditions (see SI S6). This often leads to product contamination with hard to separate oxides. In method (2) complete sulfurization is often difficult due to the limited thermal stability of H₂S and CS₂.²¹⁻²² Additional drawback is that both H₂S and CS₂ are toxic and form explosive mixtures with air.²³⁻²⁴

In studies of binary oxides, Wu and Seo described a sulfurization approach based on a solid-state metathesis reaction with boron sulfides.²⁵⁻²⁶ The O→S metathesis reaction was shown to be very effective in the sulfurization of binary oxides of transition metals and lanthanides²⁵⁻²⁶ as well as actinides.²⁷ Synthesis of α-EuZrS₃ from Eu₂O₃ and ZrO₂, in the presence of elemental boron and sulfur was also recently reported.²⁸ The approach has not yet been explored in the preparation of CPs.

In this work we investigated a preparation of sulfide CPs by solid-state reactions of ternary and binary oxides and carbonates in the presence of boron and sulfur. The synthetic approach is schematically shown in the top part of Scheme 1. In a typical reaction, ternary oxide (a), binary oxides (b), element and binary oxide (c) or carbonate (d), were thoroughly mixed



Scheme 1. Top: Diagram of the synthetic approach for preparation of CPs by sulfurization in the presence of boron. The italicized symbols A, B represent metal cations, nonitalic letter B represents boron. Bottom: Schematic energy diagram showing relative enthalpies of the sulfurization in the absence and presence of boron. Also shown are the crystal structures of a starting material ABO_3 (oxide) and the product ABS_3 (CP).

with a small (~10%) molar excess of elemental boron and stoichiometric amount of sulfur and sealed under vacuum in a quartz reaction ampule. The ampule was heated in a high-temperature furnace at 500-1100 °C for several hours to several days. The full details of the syntheses are provided in SI.

High-temperature chemistry of Boron Sulfides. As described for the first time nearly two hundred years ago,²⁹ heating of boron-sulfur mixture past the sulfur boiling point (444.6 °C) produces boron sulfides. More recent studies revealed that in vacuum, where sulfur sublimates below 120 °C, the reaction yields B₂S₃ and/or BS₂, depending on the B/S ratio in the starting mixture.³⁰ The B₂S₃ and BS₂ sublime at temperatures above 300 °C,²⁶ and form various oligomers and polymers.³¹ The high effectivity of gaseous boron sulfides as sulfurizing agents for oxides is, in part, due to a large difference in the thermodynamic stability of the byproduct B₂O₃ ($\Delta G_f^{\circ,298} = -1192.3$ kJ/mol) and B₂S₃ ($\Delta G_f^{\circ,298} = -247.6$ kJ/mol) and BS₂ ($\Delta G_f^{\circ,298} = -120$ kJ/mol).^{32-33,26} Thus, boron sulfides serve not only as a source of sulfur but also as an effective “oxygen trap”.

As shown in the bottom part of Scheme 1, the high stability of B₂O₃ makes the sulfurization of metal oxides with boron sulfides thermodynamically more favorable than the sulfurization with H₂S ($\Delta G_f^{\circ,298}(\text{H}_2\text{O}) = -228.6$ kJ/mol, $\Delta G_f^{\circ,298}(\text{H}_2\text{S}) = -33.3$ kJ/mol)³² or CS₂ ($\Delta G_f^{\circ,298}(\text{CO}_2) = -394.4$ kJ/mol, $\Delta G_f^{\circ,298}(\text{CS}_2) = 66.8$ kJ/mol)³² or direct reaction of binary sulfides. While the specific reaction mechanisms and kinetic barriers for reactions (a)-(d) are not known, comparison of reaction enthalpies calculated from available experimental and theoretical data (see SI TS7) suggests that they are highly thermodynamically favorable. This was one of the motivating factors for us to explore these processes experimentally.

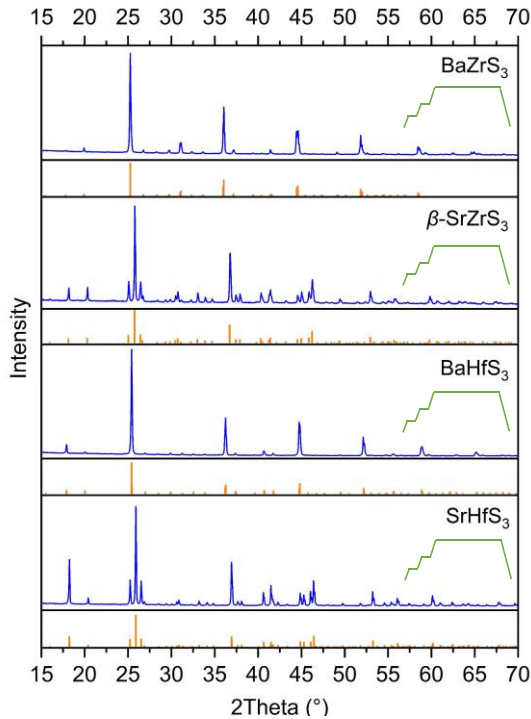
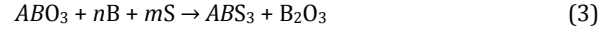


Figure 1. Powder x-ray diffraction patterns (blue traces) of the CPs prepared from the corresponding ABO_3 oxides and the reference literature patterns (orange traces) of the CPs obtained from the ICDD database. In all cases $n = 2.2$ and $m = 3$ and the heating program (schematically shown by green traces) was: ramp at 5 °C/min to 300 °C, hold 5 hrs., ramp at 5 °C/min to 600 °C, hold 5 hrs., ramp at 5 °C/min to 1000 °C, hold 36 hrs., cool down at 5 °C/min.

(a) **Sulfurization of ternary oxides ABO_3 .** Metathesis of ternary oxides was investigated for $A = \text{Ba}^{2+}$ and Sr^{2+} and $B = \text{Zr}^{4+}$ and Hf^{4+} , according to reaction (3):



In the reaction the italicized symbols A, B represent metal cations, nonitalic letter B represents boron. In the experiments the reaction mixtures were prepared with $n = 2.2$ and $m = 3$ and carried out at $T = 1000$ °C, with holding time $t = 36$ hrs. The XRD patterns of the reaction products are summarized in Fig. 1. The peaks match the reference patterns of the corresponding CPs from the ICDD database. No Bragg reflections of any other phases were detected. The product lattice parameters are in good agreement with the literature values (see SI TS1), indicating the formation of pure phases. The sharpness of the diffraction peaks and flat background indicate high degree of crystallinity of the products.

Observation of high efficiency of the metathesis reaction at $T = 1000$ °C prompted us to investigate it at more moderate temperatures, $T = 500$ -600 °C. This temperature range is an important threshold from the technological standpoint, as it represents an upper limit of thermal stability of the substrates typically used in the preparation of optoelectronic devices. The O→S metathesis of BaZrO₃ was performed according to (3), with $n = 2.2$ and $m = 3$ and temperatures and holding times systematically varied. The results are summarized in the bottom two panels of Fig. 2 and in Table TS2.

A Rietveld analysis of the XRD patterns of the reaction products for $T = 500$ °C shows that for $t = 48$ hrs. the conversion to BaZrS₃ was about ~48.5% complete and increased to ~63.8% at $t = 168$ hrs. (bottom XRD pattern in Fig. 2). The other

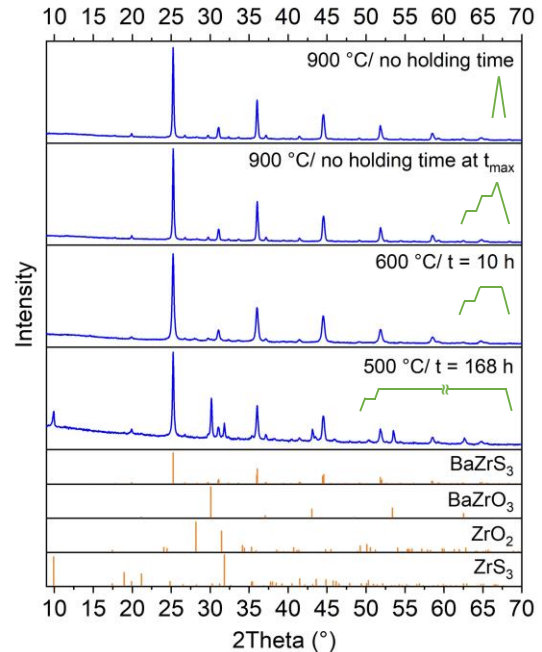


Figure 2. Sulfurization of BaZrO₃ at moderate temperatures. Powder XRD patterns (blue traces) of the reaction products as a function of reaction temperature T and holding time “ t ”. In all cases $n = 2.2$ and $m = 3$. The heating programs are schematically shown by green traces. In the bottom three panels the heating program was: ramp at 5 °C/min to 300 °C, hold 5 hrs., ramp at 5 °C/min to T , hold “ t ” hrs., cool down to RT at 5 °C/min. In the top panel the heating program was: ramp at 5 °C/min to 300 °C, cool down to RT at 5 °C/min. Also shown are reference literature patterns (orange traces) of the BaZrO₃, BaZrS₃, ZrS₃ and ZrO₂ obtained from the ICDD database.

components of the product mixture were BaZrO₃ and ZrS₃. The analysis of the results for $T = 600\text{ }^{\circ}\text{C}$ shows that at $t = 5\text{ hrs.}$ the product comprises $\sim 97\%$ of BaZrS₃. At $t = 10\text{ hrs.}$ the yield decreases to $\sim 92\%$ (XRD trace shown in Fig. 2). In both cases traces of ZrO₂ were detected in the product mixture (see Fig. S2). Other possible side products were present in the amounts below our detection limit. To find the temperature required for full conversion, the samples heated at $T = 600\text{ }^{\circ}\text{C}$ for $t = 5\text{ hrs.}$ were subsequently exposed to temperatures 650, 700, 800, 900 and 1000 $^{\circ}\text{C}$, without any holding time at maximum temperature. The experiments revealed that the complete conversion is achieved at 900 $^{\circ}\text{C}$ (Fig. 2), or above. Interestingly, the full conversion to BaZrS₃ was also achieved by a simple temperature ramp to 900 $^{\circ}\text{C}$ (at 5 $^{\circ}\text{C}/\text{min}$) without any preheating at lower temperatures (top trace in Fig. 2). Notably, this reaction, including the cool down, was complete in less than six hours (see TS2).

The above analysis leads to several observations. Although the partial conversion of BaZrO₃ to CP at $T = 500\text{ }^{\circ}\text{C}$ is encouraging, conditions for higher conversion rates and shorter reaction times have to be identified for the reaction at this temperature to be useful for applications. Increasing T to 600 $^{\circ}\text{C}$ leads to near complete conversion in as little as 5 hrs. Surprisingly, extension of the reaction time does not lead to more complete conversion. This implies a presence of a kinetic barrier, which at this temperature is difficult to overcome. Our results show that a brief heating to 900 $^{\circ}\text{C}$ is sufficient to overcome the barrier and achieve the full conversion.

To further investigate the possibility of complete BaZrO₃ \rightarrow BaZrS₃ conversion at $T = 500\text{--}600\text{ }^{\circ}\text{C}$, the reaction (3) was carried out in the presence of excess sulfur ($m = 5$). This was motivated by observations described previously in a report by Wang *et al.*,³⁴ who showed that in the reaction of BaS with ZrS₂ with excess sulfur and a small amount of BaCl₂ up to 90% conversion to BaZrS₃ can be achieved at $T = 500\text{ }^{\circ}\text{C}$ with $t = 12\text{ hrs.}$ and 96% conversion at $T = 550\text{ }^{\circ}\text{C}$ with $t = 1\text{ hr.}$ In our experiments with BaZrO₃, performed in the temperature range $T = 500\text{--}600\text{ }^{\circ}\text{C}$, with and without BaCl₂ added to the reaction mixture, we found the conversion to be more efficient without BaCl₂, with maximum conversion rate of $\sim 88\%$ at $T = 600\text{ }^{\circ}\text{C}$ and $t = 1\text{ hr.}$ At longer reaction times and lower temperatures, we observed lower conversion rates. Compared to the stoichiometric reactions described above, the reactions with excess sulfur yielded higher fractions of ZrO₂, ZrS₃ and unreacted sulfur in the product mixtures.

Our results offer some mechanistic insights. Specifically, the presence of ZrO₂ and ZrS₃ in the product mixture indicates that at least a fraction of the BaZrO₃ decomposes during the reaction. In addition, in several reactions carried out at 500–560 $^{\circ}\text{C}$ we detected small amounts of barium sulfides BaS_{*n*} ($n = 1\text{--}3$). Since no binary compounds were identified in the product mixture upon brief heating to $\geq 900\text{ }^{\circ}\text{C}$, we hypothesize the detected binary compounds are reaction intermediates. Thus, under the studied conditions one of the possible pathways for BaZrO₃ \rightarrow BaZrS₃ conversion involves initial decomposition of the former, with ZrO₂ as one of the products. Upon ZrO₂ sulfurization, the CP is likely formed by the reaction of zirconium sulfide(s) with barium sulfides. The reaction is fast at $\geq 900\text{ }^{\circ}\text{C}$, but inefficient below 600 $^{\circ}\text{C}$. Other reaction pathways may be contributing as well.

(b-d) Sulfurizations with binary oxides and carbonates. The high efficiency of sulfurization of ternary oxides prompted us to also explore similar reactions with starting materials binary oxides and carbonates, according to reactions (4)–(6):

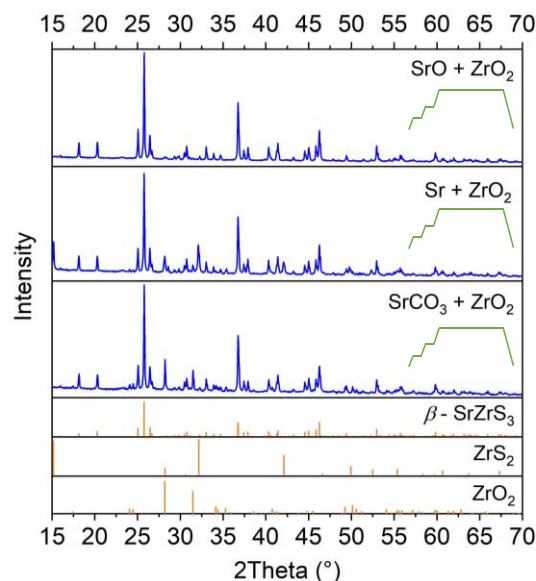
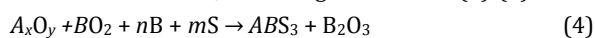
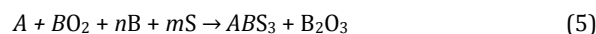


Figure 3. Effect of starting material on the sulfurization efficiency. Powder XRD patterns (blue traces) of β -SrZrS₃ CP prepared from starting materials indicated in the legends, by reaction with boron sulphides. In all cases, the heating program was: ramp at 5 $^{\circ}\text{C}/\text{min}$ to 300 $^{\circ}\text{C}$, hold 5 hrs., ramp at 5 $^{\circ}\text{C}/\text{min}$ to 600 $^{\circ}\text{C}$, hold 5 hrs., ramp at 5 $^{\circ}\text{C}/\text{min}$ to 1000 $^{\circ}\text{C}$, hold 36 hrs., cool down at 5 $^{\circ}\text{C}/\text{min}$. Also shown are reference literature patterns (orange traces) of the β -SrZrS₃, ZrS₂ and ZrO₂ obtained from the ICDD database.



The reactions were investigated for $A = \text{Ba}^{2+}$, Sr^{2+} and Eu^{3+} and $B = \text{Zr}^{4+}$ and Hf^{4+} . The details of the reaction conditions and the product compositions are summarized in SI in Tables TS3–5. The highest conversion rates to CPs were in all three types of reactions observed for $A = \text{Sr}^{2+}$ and $B = \text{Zr}^{4+}$. The XRD patterns of the products of the three reactions, carried out at $T = 1000\text{ }^{\circ}\text{C}$ and $t = 36\text{ hrs.}$, are shown in Fig. 3. The Rietveld analysis revealed that for reaction (4) the conversion rate to β -SrZrS₃ CP is $\sim 99\%$, with about 1% of ZrO₂. For reaction (5) the CP yield was 74% with $\sim 8\%$ ZrO₂ and $\sim 18\%$ ZrS₂. As the reaction (5) is thermodynamically more favorable than (4) (see TS6), the lower conversion rate suggests a larger kinetic barrier for the former. In the case of rxn. (6) the conversion rate was 82% with $\sim 18\%$ ZrO₂ in the product mixture. The lower conversion rate compared to reactions (3) and (4) may be due to a lower thermodynamic favorability (see TS6) and/or a negative effect of CO₂ formed as a side product during the reaction. Finally, we found that heating of partially oxidized binary sulfides in the presence of boron sulfides can also be used to effectively remove the oxide impurities. The details are provided in SI section 10.

In summary, we presented a new method for preparation of CPs, based on sulfurization of ternary oxides with boron sulfides in closed ampules. The method offers high conversion rates using chemically stable starting materials, significantly shorter reaction times and improved safety over the previously reported methods. Optimization of the method for synthesis at more moderate temperatures and preparation of new compositions are currently in progress.

ASSOCIATED CONTENT

Supporting Information

Synthesis details, characterization methods, reaction conditions and product composition for reactions with binary oxides and carbonates, SEM images, AES data, selected thermodynamic data. This material is available free of charge via the internet at <http://pubs.acs.org>.

AUTHOR INFORMATION

Corresponding Author

*e-mail: sykoram@uniba.sk

Author Contributions

R.B.: Conceptualization, materials synthesis, characterization, data analysis, visualization, manuscript editing. S.K.T.: Materials synthesis, visualization, manuscript editing. P.H. Materials characterization, data analysis, visualization, manuscript editing. L.V. Materials characterization, data analysis, manuscript editing. M.S. Conceptualization, funding acquisition, project administration, original manuscript writing, data analysis, visualization, editing.

Notes. The authors declare no competing financial interests.

ACKNOWLEDGMENT

This work was supported by the European Union's Horizon 2020 research and innovation programme under grant agreement no. 810701 and by the Slovak Research and Development Agency under grant agreement no. APVV-19-410. SKT acknowledges partial support from project USCCCOR (ŽoNFP: NFP313020BUZ3), co-financed by the European Regional Development Fund within the Operational Programme Integrated Infrastructure.

REFERENCES

- Green, M. A.; Ho-Baillie, A.; Snaith, H. J., The emergence of perovskite solar cells. *Nature Photonics* **2014**, *8* (7), 506-514.
- Stranks, S. D.; Snaith, H. J., Metal-halide perovskites for photovoltaic and light-emitting devices. *Nature Nanotechnology* **2015**, *10* (5), 391-402.
- Best Research-Cell Efficiency Chart. <https://www.nrel.gov/pv/cell-efficiency.html>.
- Liu, X. K.; Xu, W. D.; Bai, S.; Jin, Y. Z.; Wang, J. P.; Friend, R. H.; Gao, F., Metal halide perovskites for light-emitting diodes. *Nature Materials* **2021**, *20* (1), 10-21.
- Lei, L.; Dong, Q.; Gundogdu, K.; So, F., Metal Halide Perovskites for Laser Applications. *Adv. Funct. Mater.* **2021**, *31* (16).
- Kim, H.; Han, J. S.; Choi, J.; Kim, S. Y.; Jang, H. W., Halide Perovskites for Applications beyond Photovoltaics. *Small Methods* **2018**, *2* (3).
- Chouhan, L.; Ghimire, S.; Subrahmanyam, C.; Miyasaka, T.; Biju, V., Synthesis, optoelectronic properties and applications of halide perovskites. *Chem. Soc. Rev.* **2020**, *49* (10), 2869-2885.
- Swarnkar, A.; Mir, W. J.; Chakraborty, R.; Jagadeeswararao, M.; Sheikh, T.; Nag, A., Are Chalcogenide Perovskites an Emerging Class of Semiconductors for Optoelectronic Properties and Solar Cell? *Chem. Mater.* **2019**, *31* (3), 565-575.
- Buffiere, M.; Dhawale, D. S.; El-Mellouhi, F., Chalcogenide Materials and Derivatives for Photovoltaic Applications. *Energy Technology* **2019**, *7* (11).
- Tiwari, D.; Hutter, O. S.; Longo, G., Chalcogenide perovskites for photovoltaics: current status and prospects. *Journal of Physics-Energy* **2021**, *3* (3).
- Sopiha, K. V.; Comparotto, C.; Marquez, J. A.; Scragg, J. J. S., Chalcogenide Perovskites: Tantalizing Prospects, Challenging Materials. *Adv. Opt. Mater.* **2022**, *10* (3).
- Sun, Y. Y.; Agiorgousis, M. L.; Zhang, P. H.; Zhang, S. B., Chalcogenide Perovskites for Photovoltaics. *Nano Lett.* **2015**, *15* (1), 581-585.
- Meng, W. W.; Saparov, B.; Hong, F.; Wang, J. B.; Mitzi, D. B.; Yan, Y. F., Alloying and Defect Control within Chalcogenide Perovskites for Optimized Photovoltaic Application. *Chem. Mater.* **2016**, *28* (3), 821-829.
- Perera, S.; Hui, H. L.; Zhao, C.; Xue, H. T.; Sun, F.; Deng, C. H.; Gross, N.; Milleville, C.; Xu, X. H.; Watson, D. F.; Weinstein, B.; Sun, Y. Y.; Zhang, S. B.; Zeng, H., Chalcogenide perovskites - an emerging class of ionic semiconductors. *Nano Energy* **2016**, *22*, 129-135.
- Niu, S. Y.; Huyan, H. X.; Liu, Y.; Yeung, M.; Ye, K.; Blankemeier, L.; Orvis, T.; Sarkar, D.; Singh, D. J.; Kapadia, R.; Ravichandran, J., Bandgap Control via Structural and Chemical Tuning of Transition Metal Perovskite Chalcogenides. *Adv. Mater.* **2017**, *29* (9).
- Nishigaki, Y.; Nagai, T.; Nishiwaki, M.; Aizawa, T.; Kozawa, M.; Hanzawa, K.; Kato, Y.; Sai, H.; Hiramatsu, H.; Hosono, H.; Fujiwara, H., Extraordinary Strong Band-Edge Absorption in Distorted Chalcogenide Perovskites. *Solar Rrl* **2020**, *4* (5).
- Niu, S. Y.; Milam-Guerrero, J.; Zhou, Y. C.; Ye, K.; Zhao, B. Y.; Melot, B. C.; Ravichandran, J., Thermal stability study of transition metal perovskite sulfides. *J. Mater. Res.* **2018**, *33* (24), 4135-4143.
- Gupta, T.; Ghoshal, D.; Yoshimura, A.; Basu, S.; Chow, P. K.; Lakhnot, A. S.; Pandey, J.; Warrender, J. M.; Efstathiadis, H.; Soni, A.; Osei-Agyemang, E.; Balasubramanian, G.; Zhang, S. B.; Shi, S. F.; Lu, T. M.; Meunier, V.; Koratkar, N., An Environmentally Stable and Lead-Free Chalcogenide Perovskite. *Adv. Funct. Mater.* **2020**, *30* (23).
- Hahn, H.; Mutschke, U., Untersuchungen über ternäre chalcogenide 11. Versuche zur darstellung von thioperowskiten. *Z. Anorg. Allg. Chem.* **1956**, *288* (5-6), 269-278.
- Clearfield, A., Synthesis and crystal structures of some alkaline earth titanium and zirconium sulfides. *Acta Crystallogr.* **1963**, *16* (2), 135-&.
- Kaloidas, V. E.; Papayannakos, N. G., Hydrogen-Production from the Decomposition of Hydron-Sulfide - Equilibrium Studies on the System H₂S/H₂/SI, (I=1, ...8) in the Gas-Phase. *Int. J. Hydrogen Energy* **1987**, *12* (6), 403-409.
- Stull, D. R., Thermodynamics of Carbon Disulfide Production. *Ind. Eng. Chem.* **1949**, *41* (9), 1968-1973.
- CS₂ safety information. <https://www.osha.gov/chemicaldata/574>.
- H₂S safety information. <https://www.osha.gov/chemicaldata/652>.
- Wu, L. M.; Sharma, R.; Seo, D. K., Metathetical conversion of Nd₂O₃ nanoparticles into NdS₂ polysulfide nanoparticles at low temperatures using boron sulfides. *Inorg. Chem.* **2003**, *42* (19), 5798-+.
- Wu, L. M.; Seo, D. K., New solid-gas metathetical synthesis of binary metal polysulfides and sulfides at intermediate temperatures: Utilization of boron sulfides. *J. Am. Chem. Soc.* **2004**, *126* (14), 4676-4681.
- Breton, L. S.; Klepov, V. V.; Zur Loye, H. C., Facile Oxide to Chalcogenide Conversion for Actinides Using the Boron-Chalcogen Mixture Method. *J. Am. Chem. Soc.* **2020**, *142* (33), 14365-14373.
- Guo, S. P.; Chi, Y.; Zou, J. P.; Xue, H. G., Crystal and electronic structures, and photoluminescence and photocatalytic properties of alpha-EuZrS₃. *New J. Chem.* **2016**, *40* (12), 10219-10226.
- Berzelius, J. J., Untersuchungen über flufspathsäure und deren merkwürdigsten verbindungen *Ann. Phys.* **1824**, *78*, 113-150.
- Hurter, H. U.; Krebs, B.; Eckert, H.; Mullerwarmuth, W., Solid-State B-11 NMR-Studies on Boron Chalcogenide Systems. *Inorg. Chem.* **1985**, *24* (9), 1288-1292.
- Chen, H. Y.; Gilles, P. W., High Molecular Weight Boron Sulfides 5. Vaporization Behavior of Boron-Sulfur System. *J. Am. Chem. Soc.* **1970**, *92* (8), 2309-+.
- Barin, I., *Thermochemical Data of Pure Substances*, 3rd. Ed. VCH Verlagsgesellschaft, mbH: Weinheim, Germany, 1995.
- $\Delta G_f^{\circ,800}(\text{B}_2\text{S}_3) = -232.9 \text{ kJ/mol}$, $\Delta G_f^{\circ,1100}(\text{B}_2\text{S}_3) = -199.2 \text{ kJ/mol}$, $\Delta G_f^{\circ,800}(\text{B}_2\text{O}_3) = -1062.9 \text{ kJ/mol}$, $\Delta G_f^{\circ,1100}(\text{B}_2\text{O}_3) = -996.9 \text{ kJ/mol}$.
- Wang, Y. R.; Sato, N.; Yamada, K.; Fujino, T., Synthesis of BaZrS₃ in the presence of excess sulfur. *J. Alloys Compd.* **2000**, *311* (2), 214-223.

Synopsis. Chalcogenide perovskites with compositions $BaZrS_3$, β - $SrZrS_3$, $BaHfS_3$, $SrHfS_3$ and $EuHfS_3$ were synthesized from ternary oxides, binary oxides and carbonates in vacuum by reaction with in-situ formed boron sulfides. The new synthetic approach offers several advantages over previously reported methods, including the use of chemically stable starting materials, shorter reaction times, less hazardous preparation conditions. The effects of the of the reaction time, temperature and starting mixture composition and mechanistic insights about the reactions are discussed.

